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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:)
MAGRI' ET AL.)

Serial No. 10/749,134)
Confirmation No. 3843)
Filing Date: DECEMBER 30, 2003)

For: VERTICAL-CONDUCTION AND PLANAR)
STRUCTURE MOS DEVICE WITH A)
DOUBLE THICKNESS OF GATE OXIDE)
AND METHOD REALIZING POWER)
VERTICAL MOS TRANSISTORS WITH)
IMPROVED STATIC AND DYNAMIC)
PERFORMANCES AND HIGH SCALING)
DOWN DENSITY)

TRANSMITTAL OF FORMAL DRAWINGS

Mail Stop: PGPUB-Drawings
Commissioner for Patents
Alexandria, VA 22313-1450

Sir:

Enclosed are eight (8) sheets of formal drawings to
be filed in the above-identified patent application.

Respectfully submitted,

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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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mail in an envelope addressed to: Mail Stop: PGPUB-Drawings,
Commissioner for Patents, Alexandria, VA 22313-1450, on this
20th day of August, 2004.